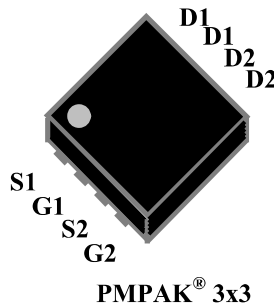


# AP0803QD

## N-Channel Power MOSFET

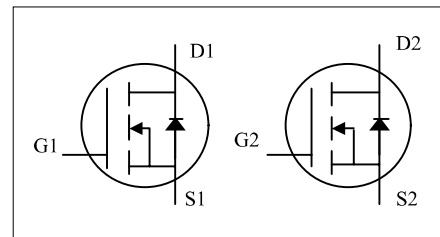
- ▼ Simple Drive Requirement
- ▼ Low On-resistance
- ▼ Fast Switching Performance
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	30V
$R_{DS(ON)}$	9m $\Omega$
$I_D$	20A

### Description

AP0803QD series are from All Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



### Absolute Maximum Ratings@T<sub>J</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Drain Current, $V_{GS} @ 10V^3$	20	A
$I_D@T_A=70^\circ C$	Drain Current, $V_{GS} @ 10V^3$	14.1	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	75	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	20	W
$E_{AS}$	Single Pulse Avalanche Energy <sup>4</sup>	65	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	6.25	$^\circ C/W$

## N-Channel Power MOSFET

Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	9	11.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	-	18	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =1mA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =10A	-	40	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =5A	-	14	22.4	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V	-	4.4	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	5.4	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =15V	-	9	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	8	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	29	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	9	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	790	1280	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V	-	225	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	160	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	2.5	5	Ω

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =10A, V <sub>GS</sub> =0V,	-	11	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	4	-	nC

## Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t<sub>l</sub> ≤10sec ; 135 °C/W when mounted on Min. copper pad.
- 4.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=15V , L=0.5mH , R<sub>G</sub>=25Ω

**N-Channel Power MOSFET**

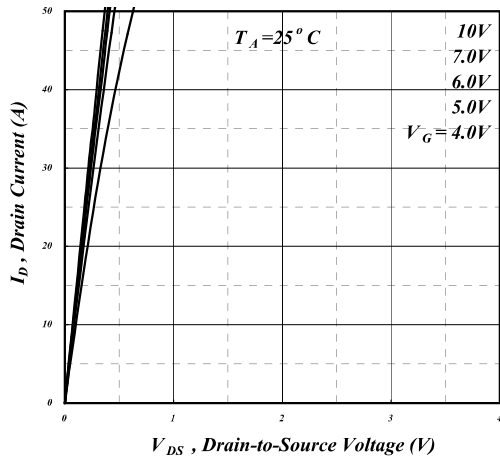


Fig 1. Typical Output Characteristics

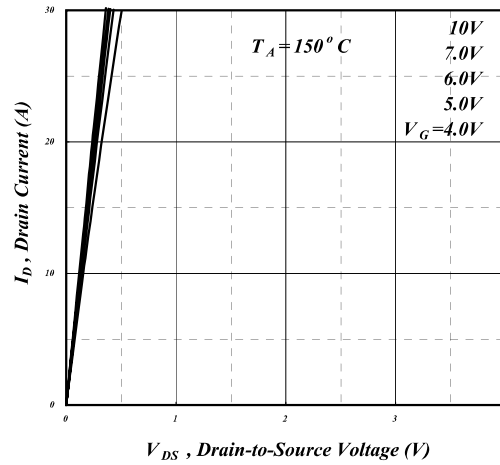


Fig 2. Typical Output Characteristics

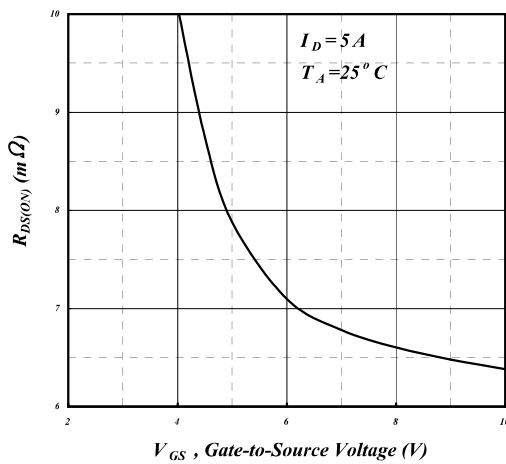


Fig 3. On-Resistance v.s. Gate Voltage

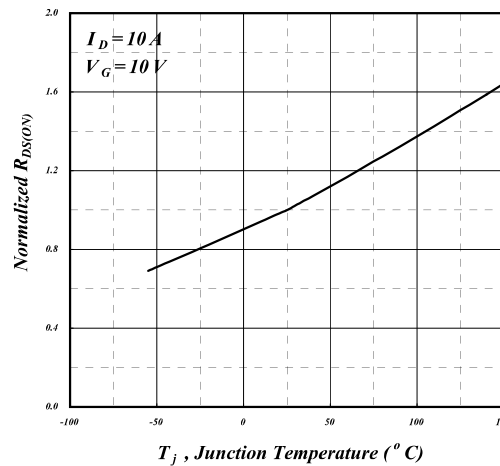


Fig 4. Normalized On-Resistance v.s. Junction Temperature

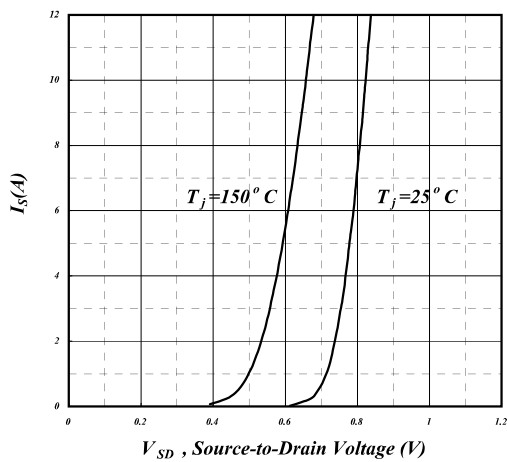


Fig 5. Forward Characteristic of Reverse Diode

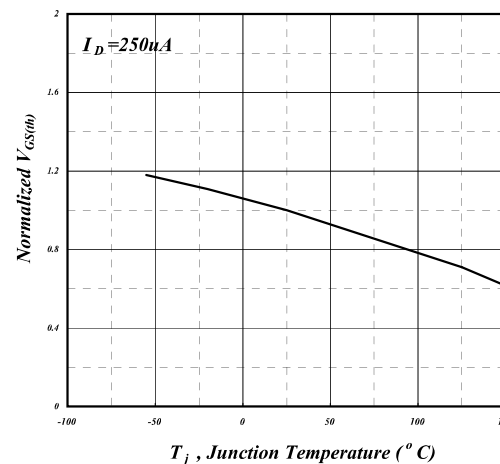
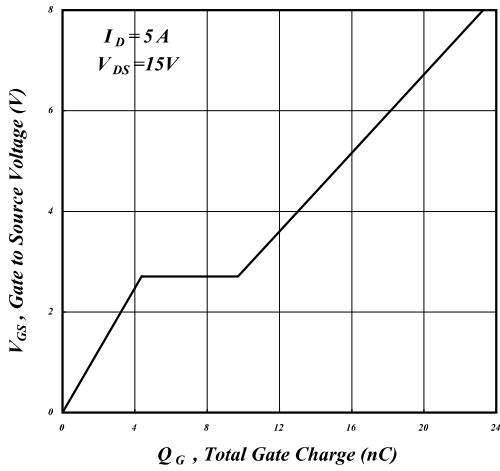
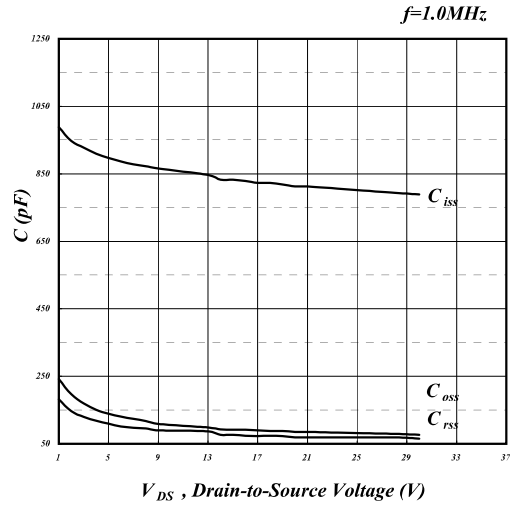


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

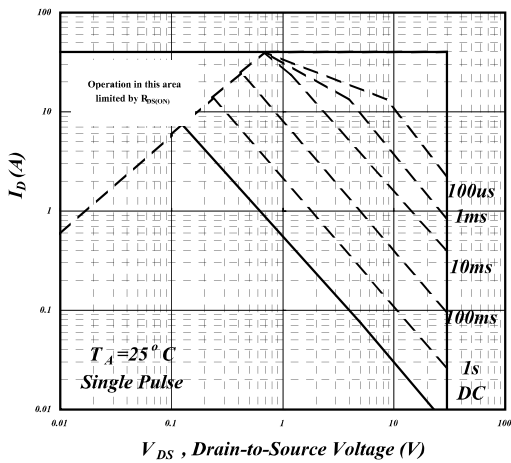
**AP0803QD**  
**N-Channel Power MOSFET**



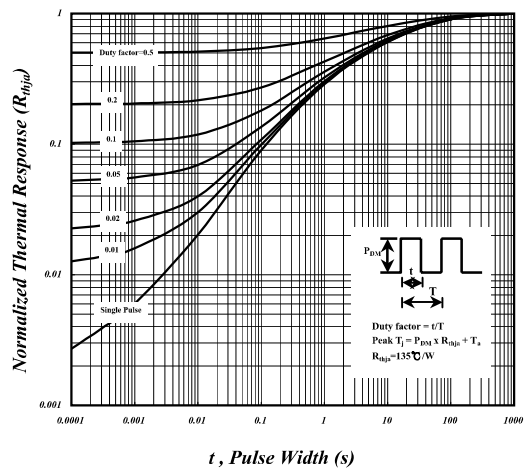
**Fig 7. Gate Charge Characteristics**



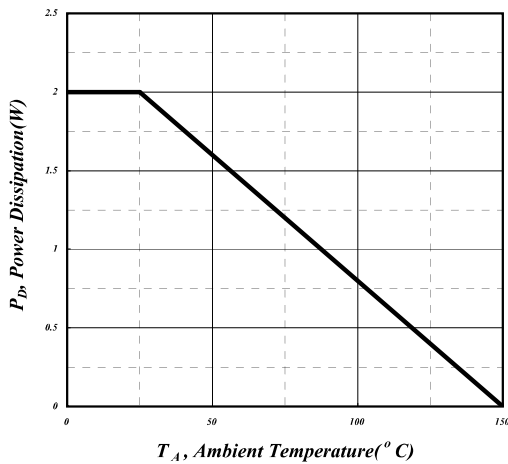
**Fig 8. Typical Capacitance Characteristics**



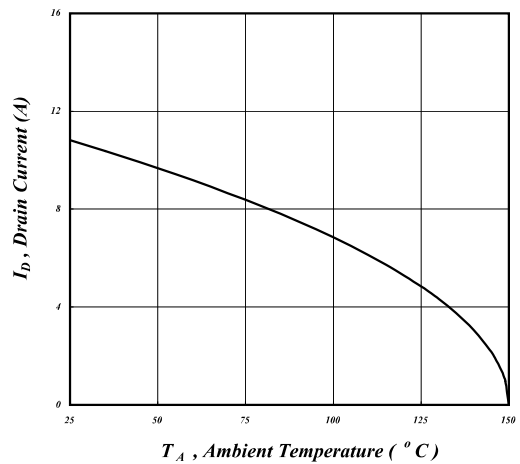
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Total Power Dissipation**

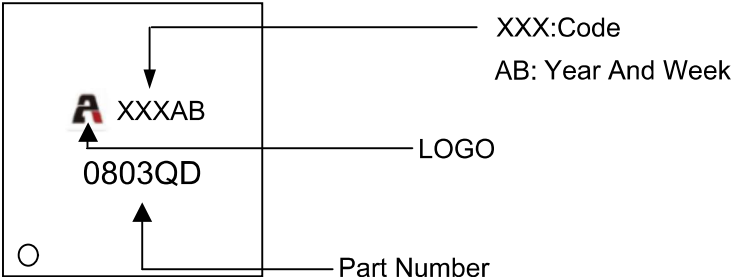


**Fig 12. Drain Current v.s. Ambient Temperature**

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**MARKING INFORMATION**



**PACKAGE OUTLINE DIMENSIONS**

